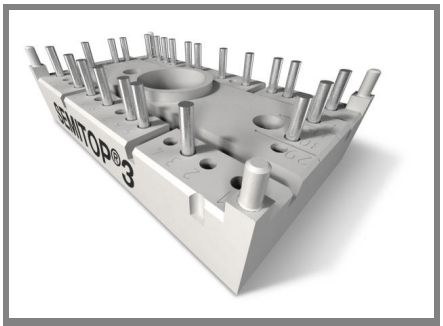
SK20MLI066



SEMITOP® 3

IGBT Module

SK20MLI066

Target Data

Features

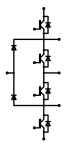
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL technology FWD

Typical Applications*

- 3 Level Inverter
- UPS

Remarks

- Visol = 3000V AC, 1s, 50Hz
- Dynamic measure: DUT= IGBT (Gate pin 1) and Neutral Clamp Diode (Kathode pin 16) as free-wheeling diode

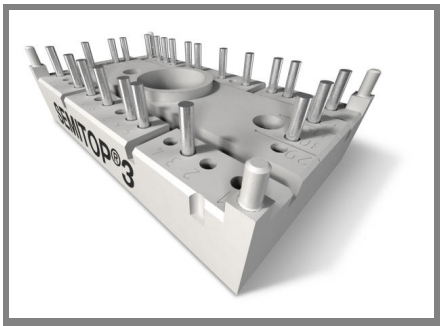


MLI

Absolute Maximum Ratings			T_s = 25 °C, unless otherwise specified	
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		600	V
I_C	T_j = 175 °C	T_s = 25 °C	30	A
		T_s = 70 °C	24	A
I_{CRM}	I_{CRM}= 2 x I_{Cnom}		40	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 360 V; $V_{GE} \leq$ 20 V; V_{CES} < 600 V	T_j = 150 °C	6	µs
Inverse Diode				
I_F	T_j = 175 °C	T_s = 25 °C	30	A
		T_s = 70 °C	24	A
I_{FRM}	I_{FRM}= 2 x I_{Fnom}		40	A
I_{FSM}	t_p = 10 ms; half sine wave	T_j = 150 °C	95	A
Freewheeling Diode				
I_F	T_j = 175 °C	T_s = 25 °C	31	A
		T_s = 70 °C	24	A
I_{FRM}	I_{FRM}= 2 x I_{Fnom}		40	A
I_{FSM}	t_p = 10 ms; half sine wave	T_j = 150 °C	95	A
Module				
$I_{t(RMS)}$				A
T_{vj}			-40 ... +175	°C
T_{stg}			-40 ... +125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics			T_s = 25 °C, unless otherwise specified			
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 0,29 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C			0,0011	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V	T_j = 25 °C			300	nA
V_{CE0}		T_j = 25 °C		0,9	1,1	V
		T_j = 150 °C		0,8	1	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		27,5	37,5	mΩ
		T_j = 150°C		40	52,5	mΩ
$V_{CE(sat)}$	I_{Cnom} = 20 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,45	1,85	V
		T_j = 150°C$_{chiplev.}$		1,65	2,05	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		1,1		nF
C_{oes}				0,071		nF
C_{res}				0,032		nF
$t_{d(on)}$	R_{Gon} = 33 Ω	V_{CC} = 300V		21		ns
t_r		I_C= 20A		19		ns
E_{on}		T_j = 150 °C		0,4		mJ
$t_{d(off)}$	R_{Goff} = 33 Ω	V_{GE}= -7/+15 V		230		ns
t_f				50		ns
E_{off}				1,07		mJ
$R_{th(j-s)}$	per IGBT			1,95		K/W

SK20MLI066



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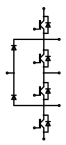

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode (Antiparallel Diode)						
$V_F = V_{EC}$	I_{Fnom} = 20 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		1,6	1,9	V
		T_j = 150 °$C_{chiplev.}$		1,65	1,95	V
V_{F0}		T_j = 25 °C		1	1,1	V
		T_j = 150 °C		0,9	1	V
r_F		T_j = 25 °C		30	40	mΩ
		T_j = 150 °C		37,5	47,5	mΩ
I_{RRM}	I_F = 20 A	T_j = 150 °C				A
Q_{rr}	di/dt = -2000 A/µs					µC
E_{rr}	V_R= 300V			0,2		mJ
$R_{th(j-s)D}$	per diode			2,46		K/W
Freewheeling Diode (Neutral Clampo diode)						
$V_F = V_{EC}$	I_{Fnom} = 20 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		1,5		V
		T_j = 150 °$C_{chiplev.}$		1,5		V
V_{F0}		T_j = 25 °C		1		V
		T_j = 150 °C		0,9		V
r_F		T_j = 25 °C		20		V
		T_j = 150 °C		25		V
I_{RRM}	I_F = 20 A	T_j = 150 °C		20		A
Q_{rr}	di/dt = -2000 A/µs			1		µC
E_{rr}	V_R=300V			0,2		mJ
$R_{th(j-s)FD}$	per diode			2,46		K/W
M_s	to heat sink		2,25		2,5	Nm
w				30		g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

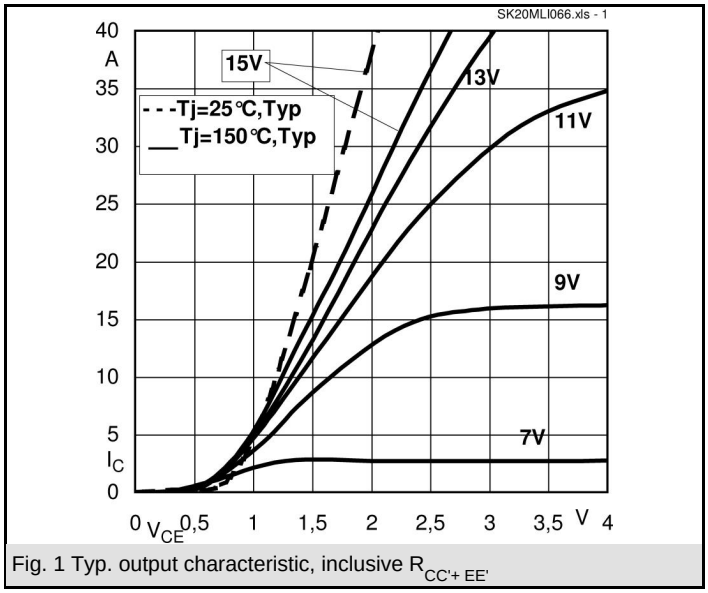


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

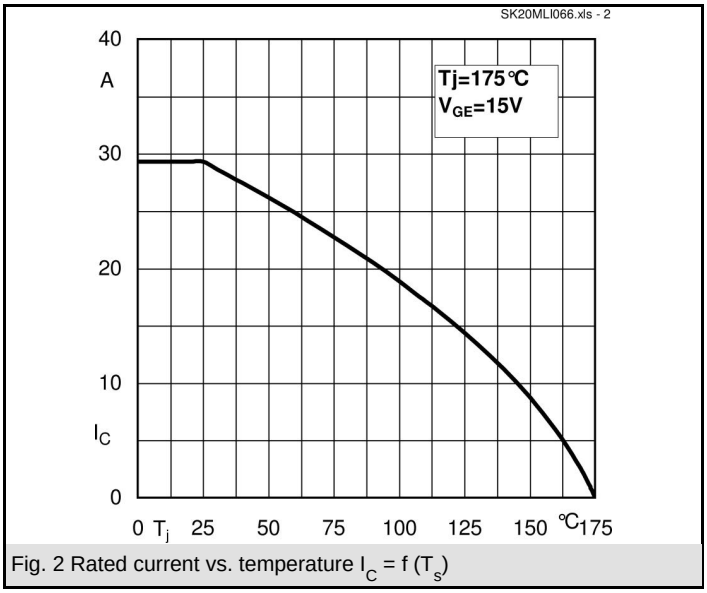


Fig. 2 Rated current vs. temperature $I_C = f(T_s)$

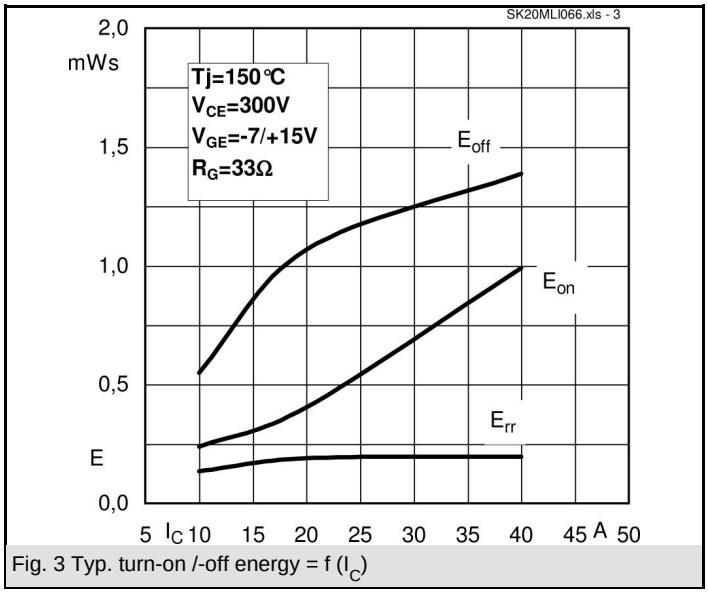


Fig. 3 Typ. turn-on /-off energy = f (I_C)

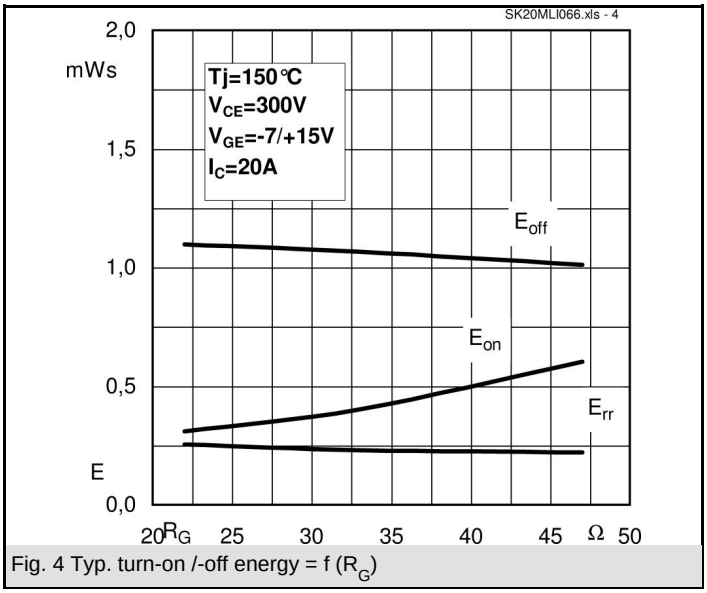


Fig. 4 Typ. turn-on /-off energy = f (R_G)

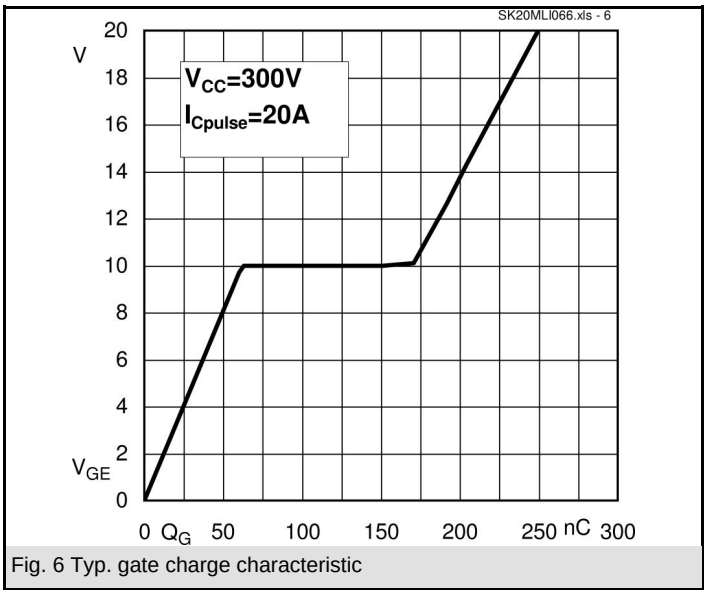


Fig. 6 Typ. gate charge characteristic

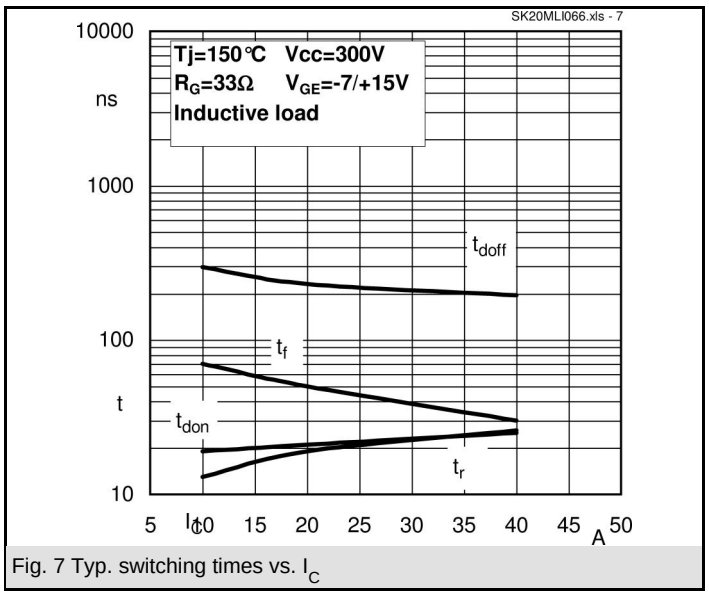


Fig. 7 Typ. switching times vs. I_C

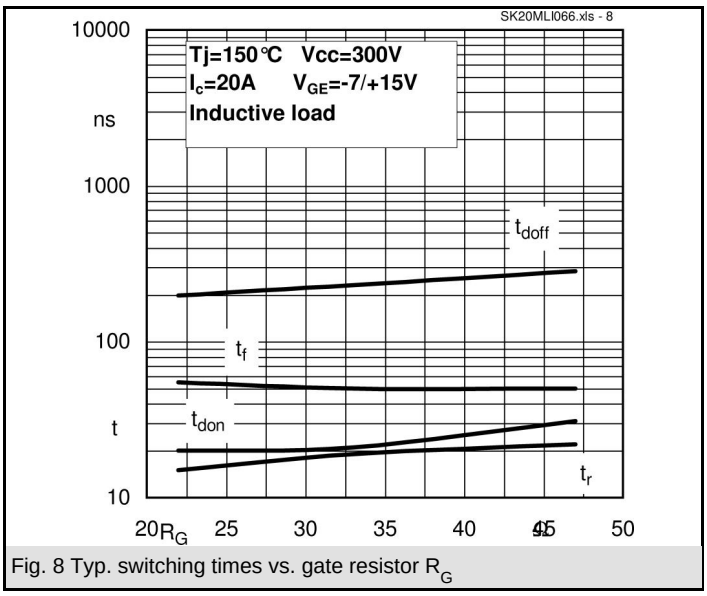


Fig. 8 Typ. switching times vs. gate resistor R_G

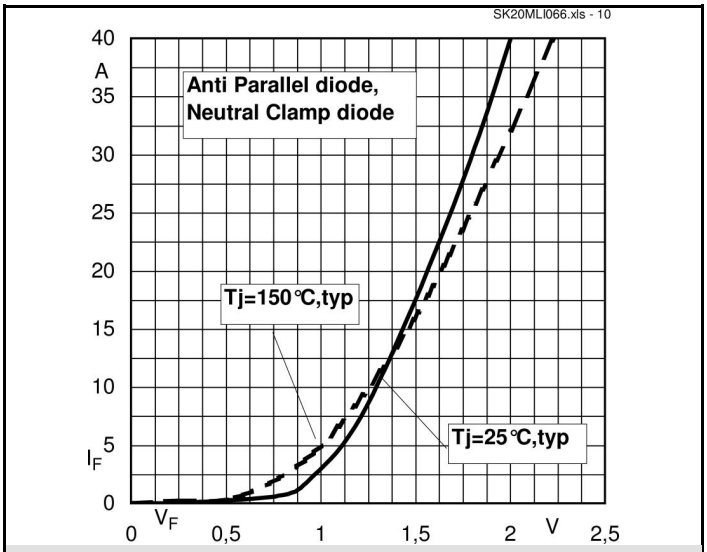
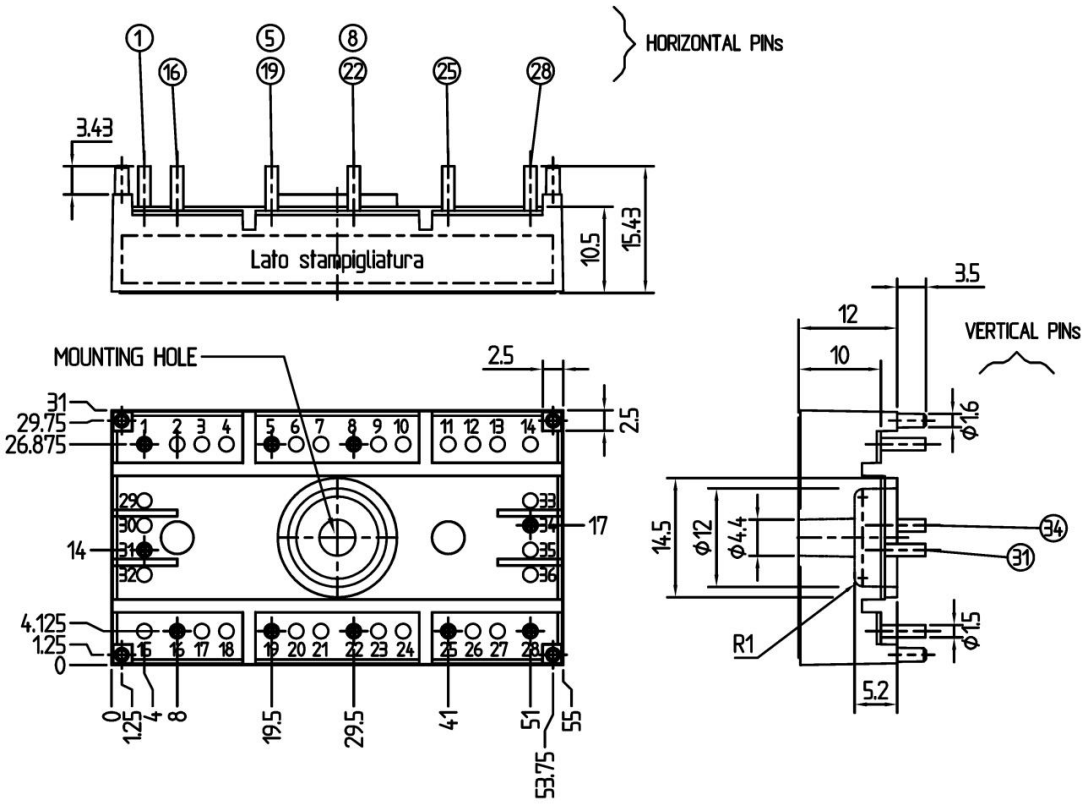
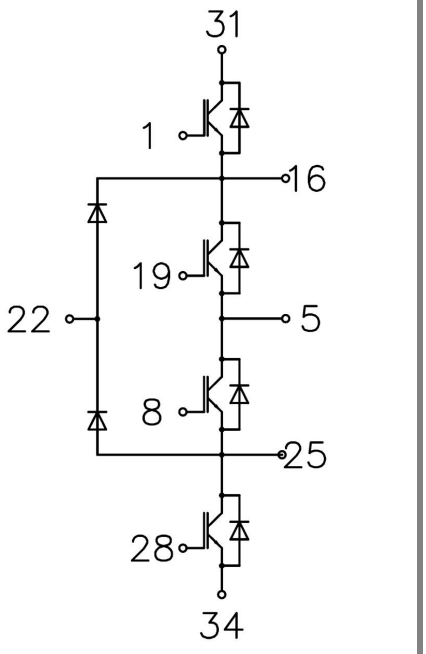


Fig. 10 CAL diode forward characteristic

Antiparallel Diode



Case T 76 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 76 MLI

